



VDRM

T(AV)

Iтsм dV/dt*

dl/dt

KEY PARAMETERS

6500V

1660A

22000A

1500V/µs

300A/µs

* Higher dV/dt selections are available on request

DCR1650C65

Replaces DS5949-4

DS5949-5 August 2023 (LN42718)

Phase Control Thyristor

FEATURES

- Double Side Cooling
- High Surge Capability

APPLICATIONS

- High Power Drives
- High Voltage Power Supplies
- Static Switches

VOLTAGE RATINGS

Part and Ordering Number	Repetitive Peak Voltages Vdrm and Vrrm (V)	Conditions
		$T_{vj} = -40^{\circ}C$ to $125^{\circ}C$,
DCR1650C65*	6500	Idrm = Irrm = 300mA,
DCR1650C60	6000	Vdrm, Vrrm tp = 10ms
DCR1650C55	5500	Vdsm & Vrsm =
DCR1650C50	5000	Vdrm & Vrrm + 100V
		respectively

Lower voltage grades available.

*6200V @ -40°C, 6500V @ 0°C

ORDERING INFORMATION

When ordering, select the required part number shown in the Voltage Ratings selection table.

For example:

DCR1650C65

Note: Please use the complete part number when ordering and quote this number in any future correspondence relating to your order.

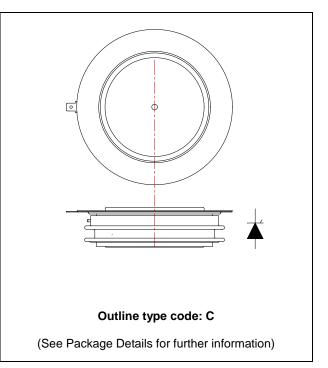


Fig. 1 Package outline

CURRENT RATINGS

T_{case} = 60°C unless stated otherwise

Symbol	Parameter	Test Conditions	Max.	Units
Double Si	de Cooled			
Ιτ(Αν)	Mean on-state current	Half wave resistive load	1660	А
It(rms)	RMS value	-	2610	А
Іт	Continuous (direct) on-state current	-	2590	А

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SURGE RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
Ітѕм	Surge (non-repetitive) on-state current	10ms half sine, Tcase = 125°C	22.0	kA
l²t	I ² t for fusing	VR = 0	2.42	MA ² s

THERMAL AND MECHANICAL RATINGS

Symbol	Parameter	Test Conditions		Min.	Max.	Units
	Rth(j-c) Thermal resistance - junction to case	Double side cooled	DC	-	10.1	°C/kW
Rth(j-c)			Anode DC	-	17.6	°C/kW
		Single side cooled	Cathode DC	-	23.9	°C/kW
	Rth(c-h) Thermal resistance - case to heatsink	Clamping force 37kN (with mounting compound)	Double side	-	2.5	°C/kW
Ktn(c-n)			Single side	-	5.0	°C/kW
Tvj	Virtual junction temperature	Blocking Vdrm / Vrrm		-	125	°C
Tstg	Storage temperature range			-55	125	°C
Fm	Clamping force			33	41	kN

DYNAMIC CHARACTERISTICS

Symbol	Parameter	Test Condition	IS	Min.	Max.	Units
Irrm/Idrm	Peak reverse and off-state current	At VRRM/VDRM, Tcase = 125°C	At Vrrm/Vdrm, Tcase = 125°C		300	mA
Vтм	Instantaneous forward voltage	At 4000A peak, Tj = 125°C		2.75	3.20	V
dV/dt	Max. linear rate of rise of off-state voltage	То 67% Vdrm, Тј = 125°С, ga	ate open	-	1500	V/µs
dl/dt	Rate of rise of on-state current	From 67% VDRM to 2x $I_{T(AV)}$ Gate source 30V, 10 Ω	Repetitive 50Hz	-	150	A/µs
airat		$tr < 0.5 \mu s, T_j = 125^{\circ}C$	Non-repetitive	-	300	A/µs
Veren	Threshold voltage - Low level	500A to 1900A at Tcase = 1	500A to 1900A at T _{case} = 125°C		1.02	V
V τ(το)	Threshold voltage - High level1900A to 7000A at Tcase = 125°C		25°C	-	1.19	V
	On-state slope resistance - Low level	500A to 1900A at T _{case} = 125°C		-	0.59	mΩ
řτ	On-state slope resistance - High level	1900A to 7000A at T _{case} = 125°C		-	0.50	mΩ
tgd	Delay time	$V_D = 67\% V_{DRM}$, gate source 30V, 10 Ω tr = 0.5µs, Tj = 25°C		-	3	μs
tq	Turn-off time	Tj = 125°C, V _R = 200V, dl/dt = 1A/µs, dV _{DR} /dt = 20V/µs linear		-	1200	μs
Qs	Stored charge	Iτ = 2000A, Tj = 125°C, dl/dt = 1A/μs		2590	5270	μC
Irr	Reverse recovery current	Vr peak ~ 4500V, Vr ~ 3000V		38	54	А
IL.	Latching current	Tj = 25°C, V _D = 5V		-	3	А
Ін	Holding current	Тј = 25°С, Rg-к = ∞, Iтм = 50	0A, I⊤ = 5A	-	300	mA

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GATE TRIGGER CHARACTERISTICS AND RATINGS

Symbol	Parameter	Test Conditions	Max.	Units
Vgt	Gate trigger voltage	VDRM = 5V, Tcase = 25°C	1.5	V
Vgd	Gate non-trigger voltage	At 50% Vdrm, Tcase = 125°C	0.4	V
Іст	Gate trigger current	Vdrm = 5V, Tcase = 25°C	350	mA
Igd	Gate non-trigger current	At 50% Vdrm, Tcase = 125°C	15	mA

CURVES

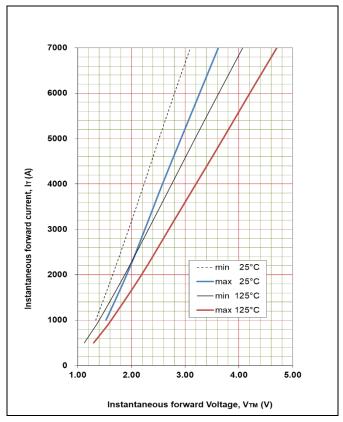


Fig. 2 Maximum & minimum on state characteristics

VTM EQUATION

$$V_{TM} = A + B.ln(I_T) + C.I_T + D.\sqrt{I_T}$$

Where A = -0.103152 B = 0.216266 C = 0.000522 D = -0.009092 These values are valid for $T_j = 125^{\circ}C$ for I_T 500A to 7000A

DCR1650C65

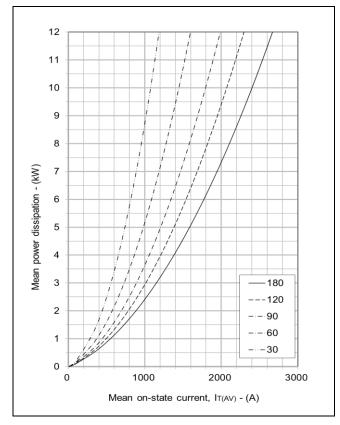


Fig. 3 On-state power dissipation - sine wave

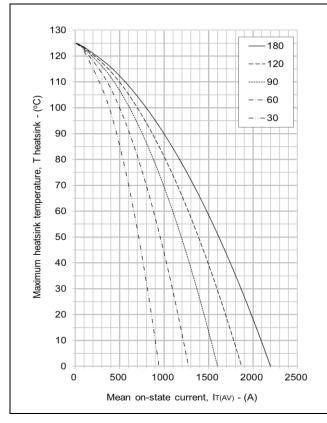


Fig. 5 Maximum permissible heatsink temperature, double side cooled - sine wave

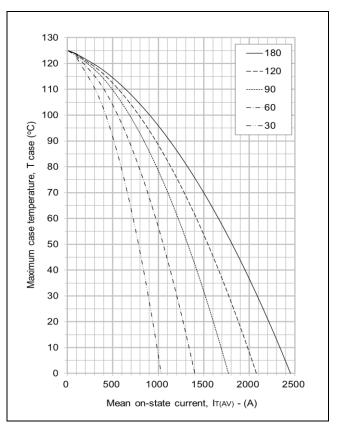


Fig. 4 Maximum permissible case temperature, double side cooled - sine wave

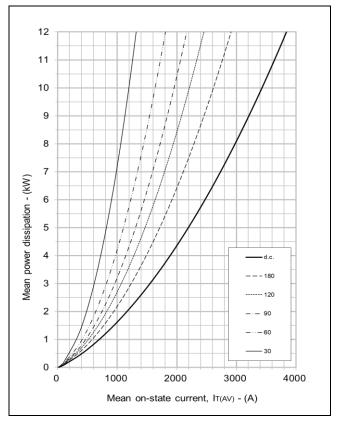


Fig. 6 On-state power dissipation - rectangular wave

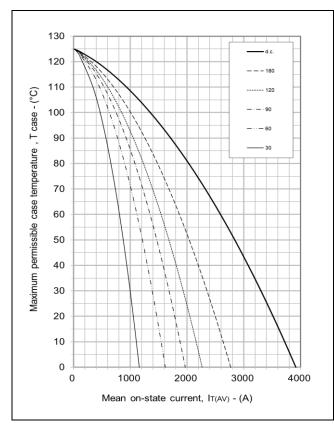
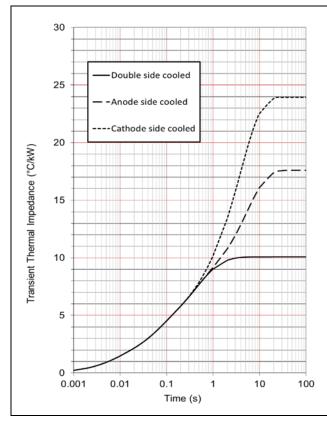


Fig. 7 Maximum permissible case temperature, double side cooled - rectangular wave



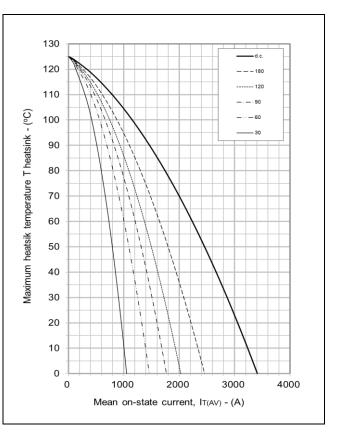


Fig. 8 Maximum permissible heatsink temperature, double side cooled - rectangular wave

		1	2	3	4
Double side	Ri(°C/kW)	1.104	2.576	4.510	1.901
cooled	Ti(s)	0.006	0.052	0.382	1.060
Anode side cooled	Ri(°C/kW)	1.098	2.457	4.047	9.999
	Ti(s)	0.006	0.050	0.313	5.270
Cathode side	Ri(°C/kW)	1.152	2.893	2.406	17.479
cooled	Ti(s)	0.006	0.058	0.378	3.970

$$Z_{th} = \sum_{i=1}^{i=4} R_i \cdot \left(1 - \exp\left(-\frac{T}{T_i}\right)\right)$$

∆R_{th(j-c)} Conduction

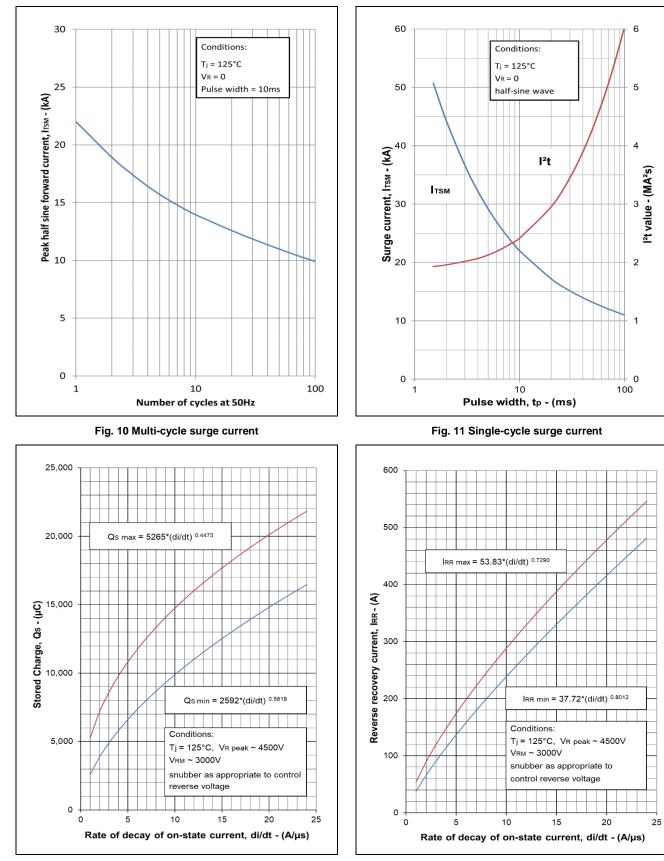
Tables show the increments of thermal resistance R $_{\text{fr}(j-q)}$ when the device operates at conduction angles other than d.c.

	Double side cooling				Anode Side	Cooling	Ca
	$\Delta Z_{th}(z)$				∆Z _{th} (z)		
θ°	sine.	rect.		θ°	sine.	rect.	θ°
180	1.95	1.26		180	1.95	1.26	180
120	2.32	1.89	[120	2.32	1.89	120
90	2.74	2.27	[90	2.74	2.27	90
60	3.14	2.70	[60	3.14	2.70	60
30	3.46	3.19	[30	3.46	3.19	30
15	3.61	3.47	[15	3.62	3.47	15

athode Sided Cooling $\Delta Z_{th}(z)$ sine rect 1.95 1.26 1.88 2.31 2.72 2.26 3.12 2.68 3.43 3.17 3 58 3 44



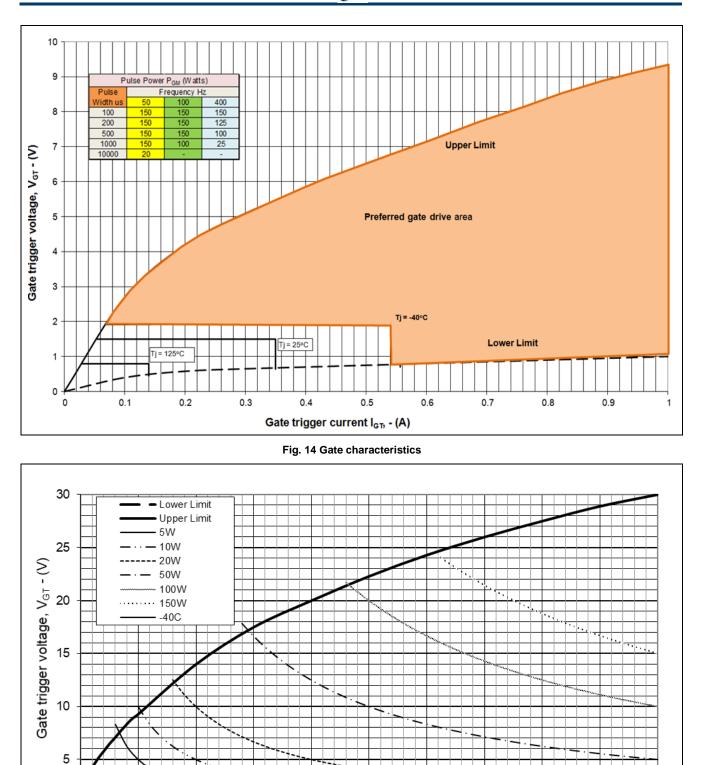
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Fig. 12 Stored charge

Fig. 13 Reverse recovery current



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4

5

6

7

8

9

2

3

0

0

1

10

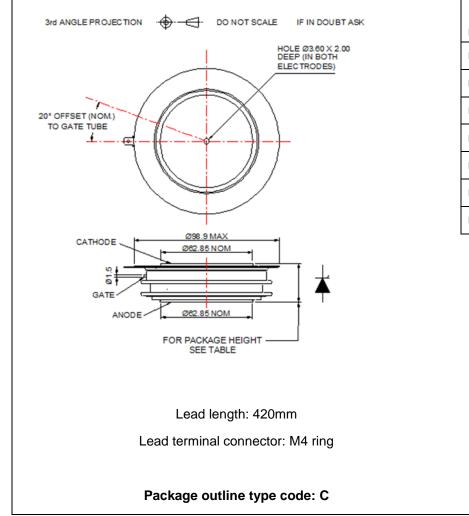
PACKAGE DETAILS

For further package information, please contact Customer services.

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All dimensions in mm, unless stated otherwise.

DO NOT SCALE



	Maximum	Minimum
	Thickness	Thickness
Device	(mm)	(mm)
DCR1370C85	27.4	26.9
DCR1650C65	27.1	26.6
DCR1950C52	26.9	26.3
DCR2150C42	26.7	26.2
DCR2630C28	26.5	26.0
DCR2860C22	26.4	25.9
DCR3370C18	26.3	25.8

Fig. 16 Package outline

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